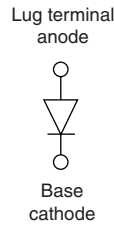


## Schottky Rectifier, 120 A


**HALF-PAK (D-67)**


### FEATURES

- 175 °C  $T_J$  operation
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Lead (Pb)-free
- Designed and qualified for industrial level


**RoHS**  
COMPLIANT

### DESCRIPTION

The 123NQ.. high current Schottky rectifier module series has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175 °C junction temperature. Typical applications are in high current switching power supplies, plating power supplies, UPS systems, converters, freewheeling diodes, welding, and reverse battery protection.

### PRODUCT SUMMARY

$I_{F(AV)}$	120 A
$V_R$	100 V

### MAJOR RATINGS AND CHARACTERISTICS

SYMBOL	CHARACTERISTICS	VALUES	UNITS
$I_{F(AV)}$	Rectangular waveform	120	A
$V_{RRM}$		100	V
$I_{FSM}$	$t_p = 5 \mu s$ sine	12 800	A
$V_F$	120 Apk, $T_J = 125 \text{ }^\circ\text{C}$	0.73	V
$T_J$	Range	- 55 to 175	$^\circ\text{C}$

### VOLTAGE RATINGS

PARAMETER	SYMBOL	123NQ100PbF	UNITS
Maximum DC reverse voltage	$V_R$	100	V
Maximum working peak reverse voltage	$V_{RWM}$		

### ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average forward current See fig. 5	$I_{F(AV)}$	50 % duty cycle at $T_C = 133 \text{ }^\circ\text{C}$ , rectangular waveform	120	A
Maximum peak one cycle non-repetitive surge current See fig. 7	$I_{FSM}$	5 $\mu s$ sine or 3 $\mu s$ rect. pulse	Following any rated load condition and with rated $V_{RRM}$ applied	12 800
		10 ms sine or 6 ms rect. pulse		1800
Non-repetitive avalanche energy	$E_{AS}$	$T_J = 25 \text{ }^\circ\text{C}$ , $I_{AS} = 5.5 \text{ A}$ , $L = 1 \text{ mH}$	15	mJ
Repetitive avalanche current	$I_{AR}$	Current decaying linearly to zero in 1 $\mu s$ Frequency limited by $T_J$ maximum $V_A = 1.5 \times V_R$ typical	1	A

ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum forward voltage drop See fig. 1	$V_{FM}^{(1)}$	120 A	$T_J = 25\text{ }^\circ\text{C}$	0.91	V
		240 A		1.26	
		120 A	$T_J = 125\text{ }^\circ\text{C}$	0.73	
		240 A		0.9	
Maximum reverse leakage current See fig. 2	$I_{RM}$	$T_J = 25\text{ }^\circ\text{C}$	$V_R = \text{Rated } V_R$	3	mA
		$T_J = 125\text{ }^\circ\text{C}$		40	
Maximum junction capacitance	$C_T$	$V_R = 5 V_{DC}$ (test signal range 100 kHz to 1 MHz) 25 °C		2650	pF
Typical series inductance	$L_S$	From top of terminal hole to mounting plane		7.0	nH
Maximum voltage rate of change	dV/dt	Rated $V_R$		10 000	V/ $\mu$ s

**Note**

(1) Pulse width = 500  $\mu$ s

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS		
Maximum junction and storage temperature range	$T_J, T_{Stg}$			- 55 to 175	°C		
Maximum thermal resistance, junction to case	$R_{thJC}$	DC operation See fig. 4		0.38	°C/W		
Typical thermal resistance, case to heatsink	$R_{thCS}$	Mounting surface, smooth and greased		0.05			
Approximate weight				30	g		
				1.06	oz.		
Mounting torque	minimum	Non-lubricated threads		3 (26.5)	N · m (lbf · in)		
	maximum			4 (35.4)			
Terminal torque	minimum			3.4 (30)			
	maximum			5 (44.2)			
Case style							HALF-PAK module

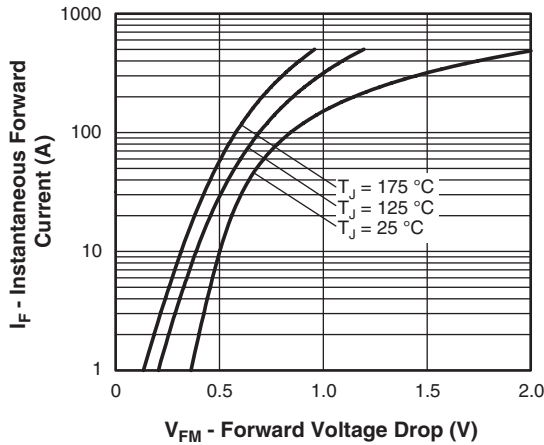


Fig. 1 - Maximum Forward Voltage Drop Characteristics

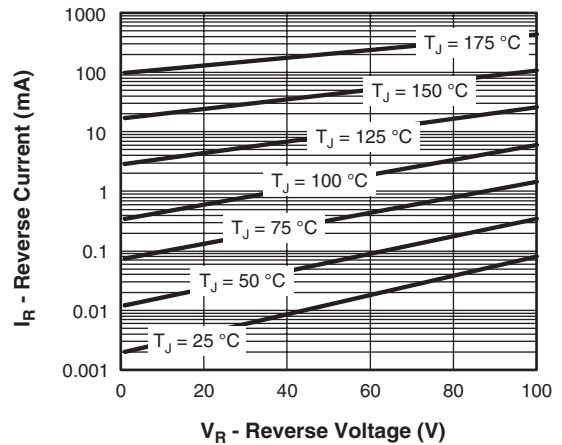


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

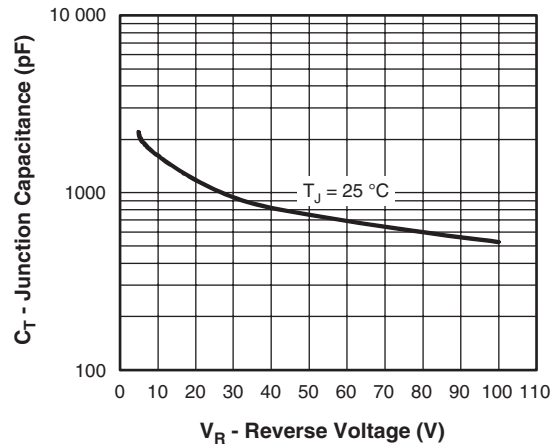


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

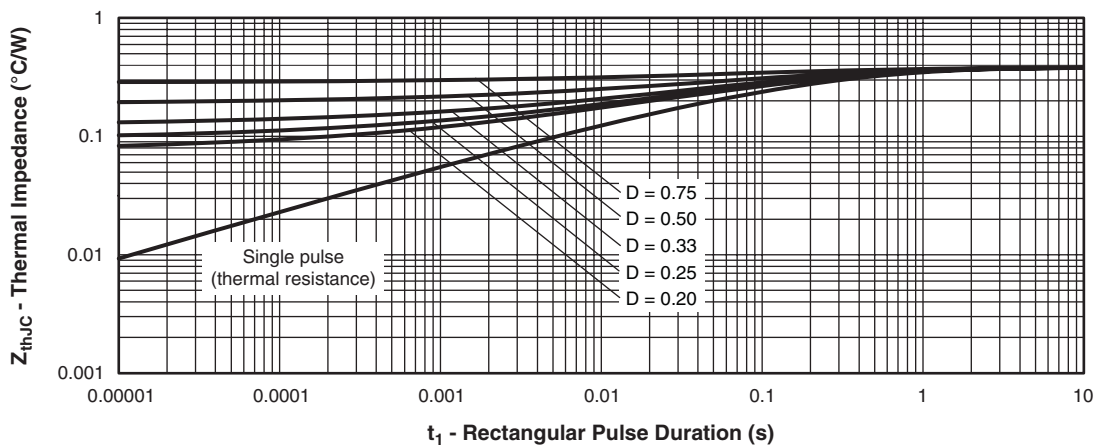


Fig. 4 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics

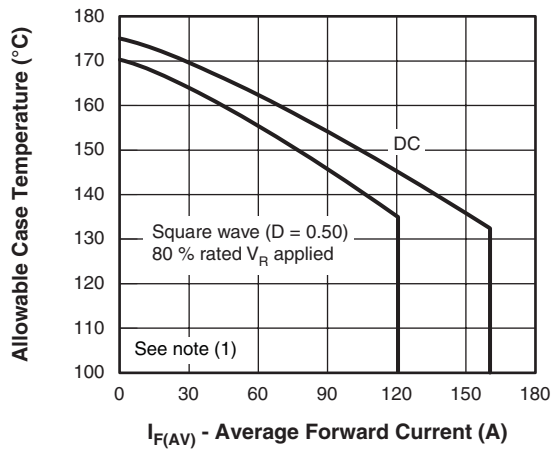


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

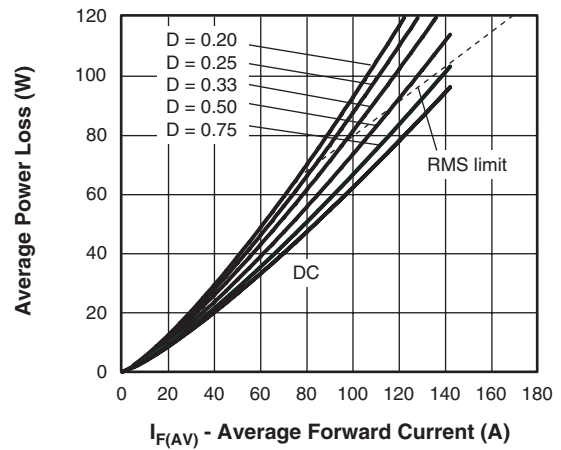


Fig. 6 - Forward Power Loss Characteristics

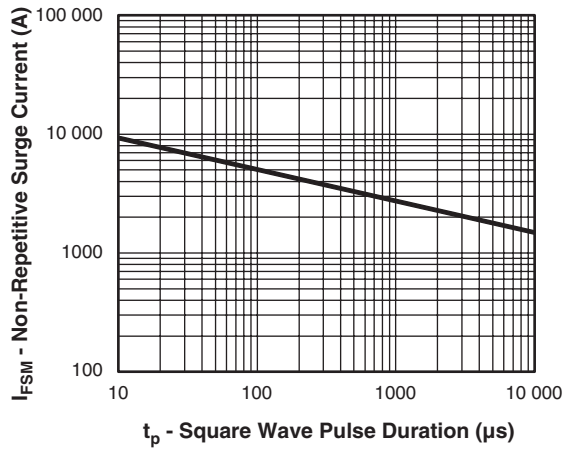


Fig. 7 - Maximum Non-Repetitive Surge Current

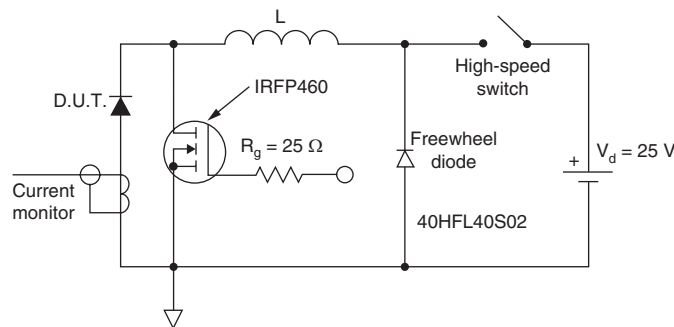


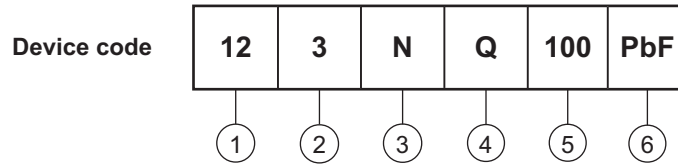
Fig. 8 - Unclamped Inductive Test Circuit

**Note**

- (1) Formula used:  $T_C = T_J - (P_d + P_{d_{REV}}) \times R_{thJC}$ ;  
 $P_d$  = Forward power loss =  $I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig. 6);  
 $P_{d_{REV}}$  = Inverse power loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1}$  = Rated  $V_R$



**ORDERING INFORMATION TABLE**



- 1** - Average current rating (x 10)
- 2** - Product silicon identification
- 3** - N = Not isolated
- 4** - Q = Schottky rectifier diode
- 5** - Voltage rating (100 = 100 V)
- 6** - Lead (Pb)-free

LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?95020">http://www.vishay.com/doc?95020</a>



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